

产品概览

NCP51705: SiC MOSFET 驱动器，低压侧，单个 6 A 高速

欲看完整文档，请参阅数据表。

NCP51705 驱动器主要用于驱动 SiC MOSFET 晶体管。为了实现最低的导通损耗，该驱动器能够为 SiC MOSFET 器件提供最大门极电压。通过在开启和关断期间提供高峰值电流，开关损耗也得以最大程度减少。为了提高可靠性，dV/dt 抗扰性甚至更快的关断时间，NCP51705 可以使用板上电荷泵来产生用户可选择的负电压轨。对于隔离应用，NCP51705 还提供了外部可访问的 5 V 轨，为数字或高速光隔离器辅助侧供电。

特性

- High Peak Output Current with Split Output Stages
- Extended Positive Voltage Rating up to 28 V Max
- User-adjustable Built-in Negative Charge Pump (-3.3 V to -8 V)
- Accessible 5 V Reference / Bias Rail
- Adjustable Under-Voltage Lockout
- Fast Desaturation Function
- QFN24 Package 4 x 4 mm

优势

- Allow independent Turn-ON/Turn-OFF Adjustment
- Efficient SiC MOSFET Operation during the Conduction Period
- Fast Turn-off and Robust dV/dt Immunity
- Minimize complexity of bias supply in isolated gate drive applications
- Sufficient VGS amplitude to match SiC best performance
- Self protection of the design
- Small & Low Parasitic Inductance package

应用

- High Performance Inverters
- High Power Motor Drivers
- Totem Pole PFC

终端产品

- Industrial & Motor Drives
- UPS & Solar Inverters
- High Power DC Chargers

器件电气规格

产品	Pricing (\$/Unit)	Compliance	Status	Power Switch	Number of Outputs	Topology	Isolation Type	V _{in} Max (V)	V _{cc} Max (V)	Rise Time (ns)	Fall Time (ns)	Drive Source Current Typ (A)	Drive Sink Current Typ (A)	Turn On Prop. Delay Typ (ns)	Turn Off Prop. Delay Typ (ns)	Delay Matching	Package Type
NCP51705MNTXG	1.6133	Pb-free Halide free non AEC-Q and PPAP	Active	SiC MOSFET	1	Single	Non-Isolated	N/A	28	8	8	6	6	25	25		WQFN-24

欲了解更多信息，请联系您当地的销售支援 www.onsemi.cn。

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